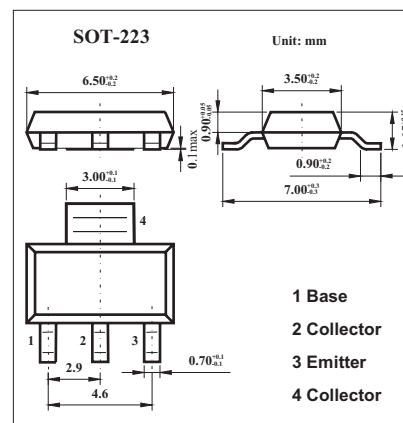


PNP High-Voltage Transistor

BSP16

■ Features

- High voltage (max. 350 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
collector-base voltage (open emitter)	V _{CB0}	-350	V
collector-emitter voltage (open base)	V _{CE0}	-300	V
emitter-base voltage (open collector)	V _{EB0}	-6	V
collector current (DC)	I _C	-200	mA
base current (DC)	I _B	-200	mA
total power dissipation T _{amb} ≤ 25 °C *	P _{tot}	1.28	W
storage temperature	T _{stg}	-65 to 150	°C
junction temperature	T _j	150	°C
operating ambient temperature	T _{amb}	-65 to 150	°C
thermal resistance from junction to ambient *	R _{th j-a}	97	K/W
thermal resistance from junction to soldering point	R _{th j-s}	16	K/W

* . Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm².

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
collector cut-off current	I _{CBO}	I _E = 0; V _{CB} = -280 V			-100	nA
emitter cut-off current	I _{EBO}	I _C = 0; V _{EB} = -6 V			-100	nA
DC current gain	h _{FE}	I _C = -50 mA; V _{CE} = -10 V	30		120	
collector-emitter saturation voltage	V _{CEsat}	I _C = -50 mA; I _B = -5 mA			-2	V
collector capacitance	C _c	I _E = I _E = 0; V _{CB} = -10 V; f = 1 MHz			15	pF
transition frequency	f _T	I _C = -10 mA; V _{CE} = -10 V; f = 100 MHz	15			MHz